

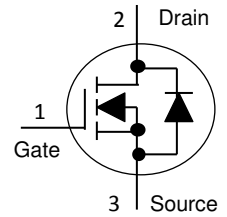
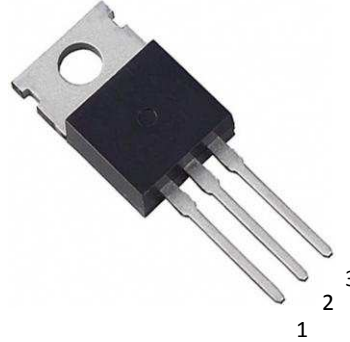
**75V / 75A**  
**N-Channel Enhancement Mode MOSFET**

75V,  $R_{DS(ON)}=9.0m\Omega@V_{GS}=10V, I_D=20A$

### Features

- Low On-State Resistance
- Excellent Gate Charge x  $R_{DS(ON)}$  Product ( FOM )
- Fully Characterized Avalanche Voltage and Current
- Specially Designed for DC-DC Converter, Off-line UPS, Automotive System, Solenoid and Motor Control
- In compliance with EU RoHs 2002/95/EC Directives

### TO-220AB



### Mechanical Information

- Case: TO-220AB Molded Plastic
- Terminals : Solderable per MIL-STD-750, Method 2026

### Marking & Ordering Information

TYPE	MARKING	PACKAGE	PACKING
HY75N075T	75N075T	TO-220AB	50PCS/TUBE

### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ unless otherwise specified )

Parameter	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	75	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1)</sup>	$I_D$	75	A
Pulsed Drain Current <sup>1)</sup>	$I_{DM}$	300	A
Maximum Power Dissipation Derating Factor	$P_D$	83.3 0.56	W
Avalanche Energy with Single Pulse, $L=0.1\text{mH}$	$E_{AS}$	420	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to +175	$^\circ\text{C}$

Note : 1. Maximum DC current limited by the package

### Thermal Characteristics

Parameter	Symbol	Value	Units
Junction-to-Case Thermal Resistance	$R_{\theta JC}$	1.8	$^\circ\text{C}/\text{W}$
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$

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**Electrical Characteristics (  $T_C=25^{\circ}\text{C}$  , Unless otherwise noted )**

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V \cdot I_D=250\mu A$	75	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS} \cdot I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V \cdot I_D=20A$	-	7.4	9.0	m $\Omega$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=60V \cdot V_{GS}=0V$	-	-	1	$\mu A$
Gate Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V \cdot V_{DS}=0V$	-	-	$\pm 100$	nA
<b>Dynamic</b>						
Total Gate Charge	Qg	$V_{DS}=30V \cdot I_D=20A$ $V_{GS}=10V$	-	82	-	nC
Gate-Source Charge	Qgs		-	23.6	-	
Gate-Drain Charge	Qgd		-	22	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=30V \cdot I_D=20A$ $V_{GS}=10V \cdot R_G=3.6\Omega$	-	28.6	-	ns
Turn-On Rise Time	$t_r$		-	19.2	-	
Turn-Off Delay Time	$t_{d(off)}$		-	86	-	
Turn-Off Fall Time	$t_f$		-	46	-	
Input Capacitance	$C_{iss}$	$V_{DS}=30V \cdot V_{GS}=0V$ $f=1.0\text{MHz}$	-	4250	-	pF
Output Capacitance	$C_{oss}$		-	650	-	
Reverse Transfer Capacitance	$C_{rss}$		-	330	-	
Gate Resistance	Rg		-	1.5	-	$\Omega$
<b>Source-Drain Diode</b>						
Max. Diode Forward Voltage	$I_S$	-	-	-	75	A
Diode Forward Voltage	$V_{SD}$	$I_S=20A \cdot V_{GS}=0V$	-	0.82	1.4	V
Reverse Recovery Time	$t_{rr}$	$V_{GS}=0V \cdot I_S=20A$ $di/dt=100A/\mu s$	-	36	-	ns
Reverse Recovery Charge	$Q_{rr}$		-	55	-	$\mu C$

**NOTE** : Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$

## Typical Characteristics Curves ( $T_c=25^\circ\text{C}$ , unless otherwise noted)

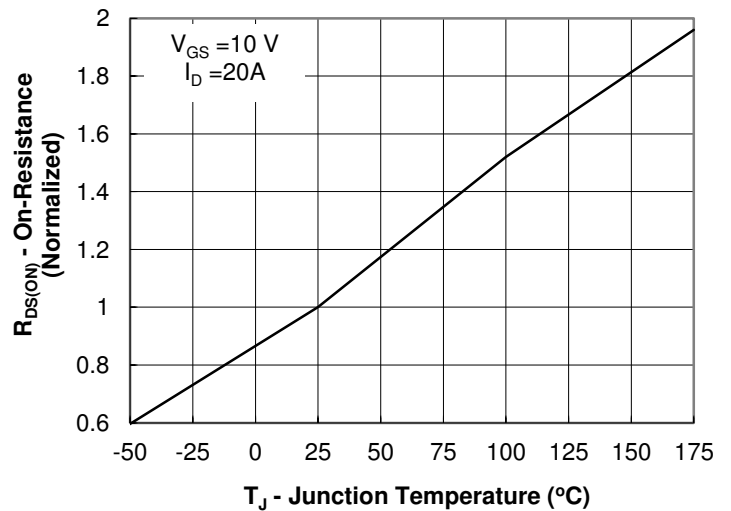
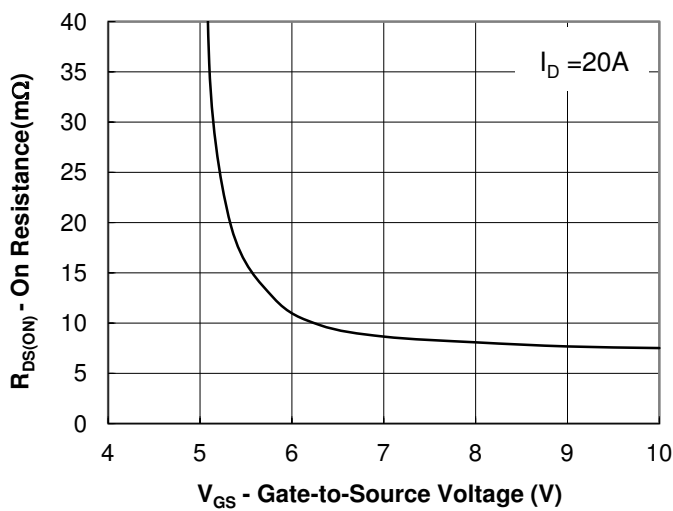
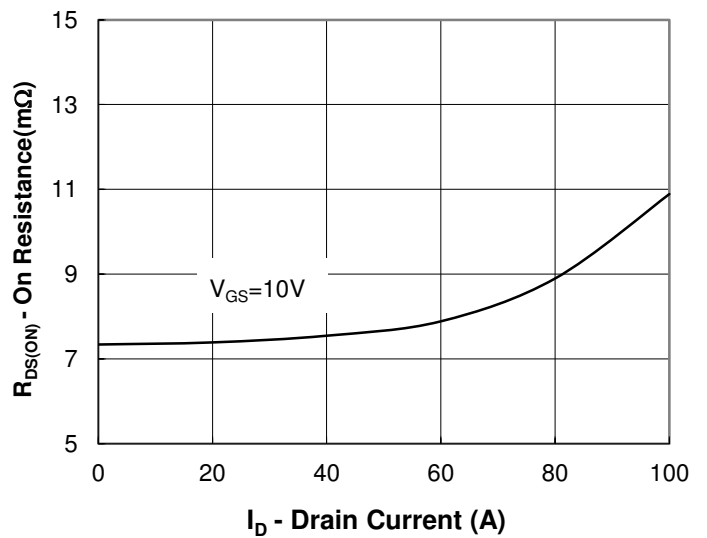
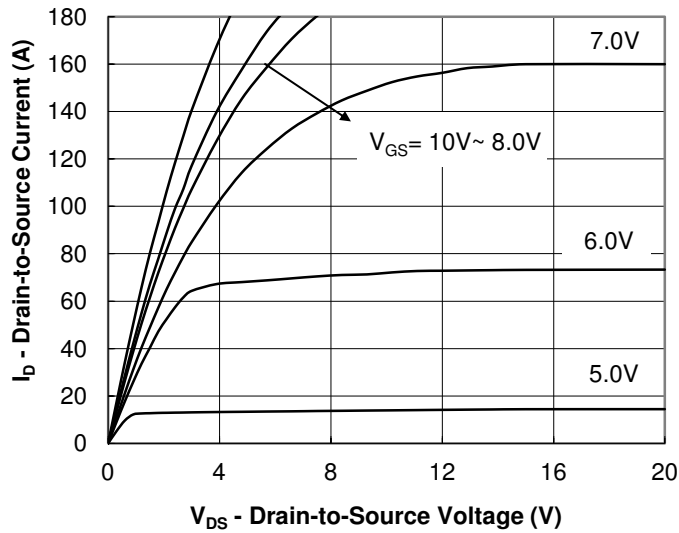


Fig.3 On-Resistance vs Gate to Source Voltage

Fig.4 On-Resistance vs Junction Temperature

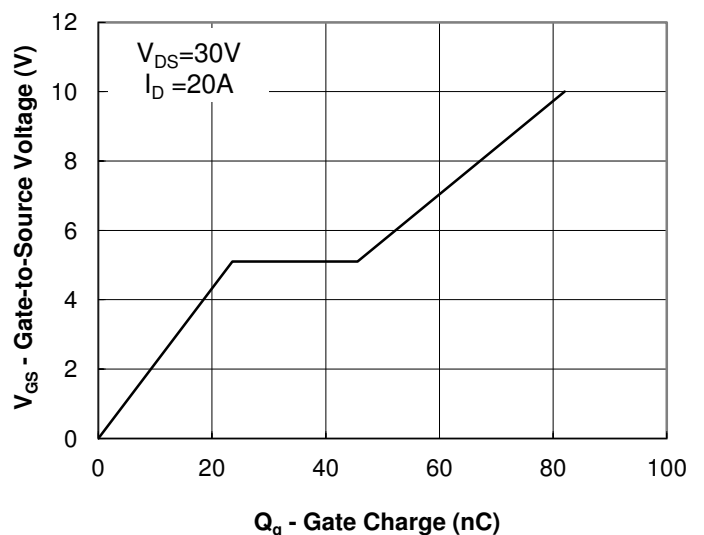
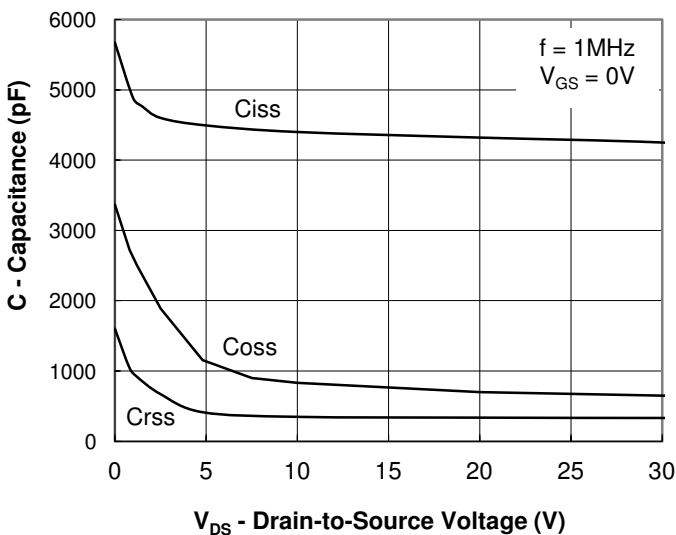
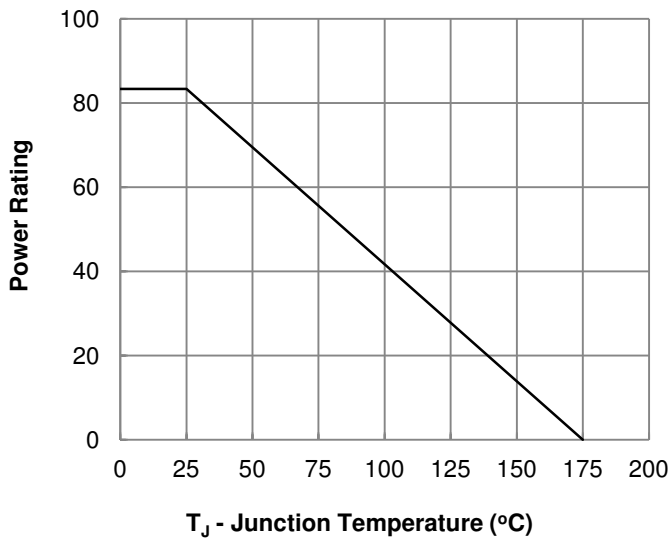


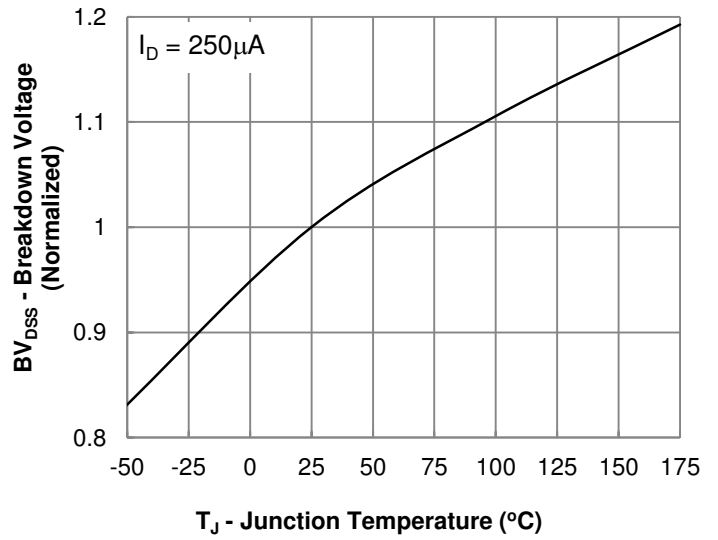
Fig.5 Capacitance Characteristic

Fig.6 Gate Charge Characteristic

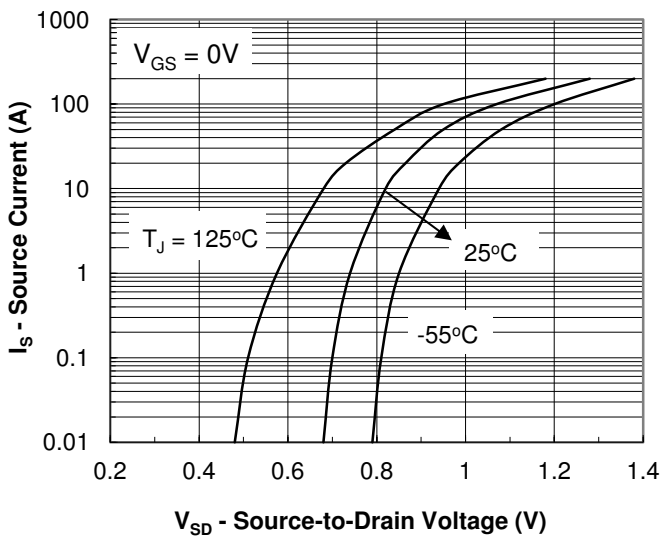
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**Fig.7 Power Derating Curve**



**Fig.8 Breakdown Voltage vs Junction Temperature**



**Fig.9 Body Diode Forward Voltage Characteristic**